

4-22-02

G/1765
AF
1708
#10/c
4/25/02



1

MEMC 99-0900 (2632)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Fuerhoff et al.

Art Unit 1765

Serial No. 09/502,340

Filed February 10, 2000

For METHOD AND APPARATUS FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS

Examiner M. Anderson

April 19, 2002

AMENDMENT B UNDER 37 CFR § 1.116

RECEIVED

APR 25 2002

TC 1700

TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

In response to the final Office action mailed February 20, 2002, please enter the following amendments:

IN THE CLAIMS

Please amend claims 1 and 9 as follows:

5/20/02
1. A method for use in combination with a crystal growing apparatus for growing a monocrystalline ingot according to the Czochralski process, said crystal growing apparatus having a heated crucible containing a semiconductor melt from which the ingot is grown, said ingot being grown on a seed crystal pulled from the melt, said method comprising the steps of:

C1
defining a temperature model representative of variations in the temperature of the melt in response to variations in power supplied to a heater for heating the melt;

pulling the ingot from the melt at a target pull rate, said target pull rate substantially following a velocity profile, said velocity profile stored in memory and defining the target pull rate as a function of the length of the ingot during pulling;